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International
IOR Rectifier

PD- 91579A

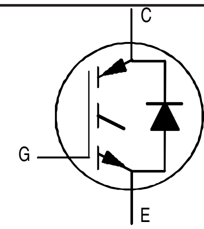
IRG4PH30KD

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT

Features

- High short circuit rating optimized for motor control, t_{sc} =10µs, V_{CC} = 720V , T_J = 125°C, V_{GE} = 15V
- Combines low conduction losses with high switching speed
- Tighter parameter distribution and higher efficiency than previous generations
- IGBT co-packaged with HEXFRED^{TM} ultrafast, ultrasoft recovery antiparallel diodes



n-channel

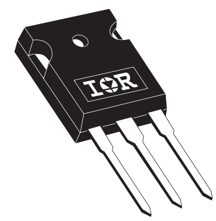
V_{CES} = 1200V

$V_{CE(on)\ typ.}$ = 3.10V

@V_{GE} = 15V, I_C = 10A

Benefits

- Latest generation 4 IGBT's offer highest power density motor controls possible
- HEXFRED^{TM} diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise, EMI and switching losses
- This part replaces IRGPH30MD2 products
- For hints see design tip 97003


TO-247AC

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
I_C @ T_C = 25°C	Continuous Collector Current	20	A
I_C @ T_C = 100°C	Continuous Collector Current	10	
I_{CM}	Pulsed Collector Current ①	40	
I_{LM}	Clamped Inductive Load Current ②	40	
I_F @ T_C = 100°C	Diode Continuous Forward Current	10	
I_{FM}	Diode Maximum Forward Current	40	
t_{sc}	Short Circuit Withstand Time	10	µs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
P_D @ T_C = 25°C	Maximum Power Dissipation	100	W
P_D @ T_C = 100°C	Maximum Power Dissipation	42	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{θJC}$	Junction-to-Case - IGBT	——	——	1.2	°C/W
$R_{θJC}$	Junction-to-Case - Diode	——	——	2.5	
$R_{θCS}$	Case-to-Sink, flat, greased surface	——	0.24	——	
$R_{θJA}$	Junction-to-Ambient, typical socket mount	——	——	40	
Wt	Weight	——	6 (0.21)	——	g (oz)

2/7/2000

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage③	1200	—	—	V	V_{GE} = 0V, I_C = 250µA	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.19	—	V/°C	V_{GE} = 0V, I_C = 1.0mA	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	3.10	4.2	V	I_C = 10A	V_{GE} = 15V
		—	3.90	—		I_C = 20A	See Fig. 2, 5
		—	3.01	—		I_C = 10A, T_J = 150°C	
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		V_{CE} = V_{GE}, I_C = 250µA	
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-12	—	mV/°C	V_{CE} = V_{GE}, I_C = 250µA	
g_{fe}	Forward Transconductance ④	4.3	6.5	—	S	V_{CE} = 100V, I_C = 10A	
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	µA	V_{GE} = 0V, V_{CE} = 1200V	
		—	—	3500		V_{GE} = 0V, V_{CE} = 1200V, T_J = 150°C	
V_{FM}	Diode Forward Voltage Drop	—	3.4	3.8	V	I_C = 10A	See Fig. 13
		—	3.3	3.7		I_C = 10A, T_J = 150°C	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V	

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
Q_g	Total Gate Charge (turn-on)	—	53	80	nC	I_C = 10A	
Q_{ge}	Gate - Emitter Charge (turn-on)	—	9.0	14		V_{CC} = 400V See Fig.8	
Q_{gc}	Gate - Collector Charge (turn-on)	—	21	32		V_{GE} = 15V	
$t_{d(on)}$	Turn-On Delay Time	—	39	—	ns		
t_r	Rise Time	—	84	—		T_J = 25°C	
$t_{d(off)}$	Turn-Off Delay Time	—	220	340		I_C = 10A, V_{CC} = 800V	
t_f	Fall Time	—	90	140		V_{GE} = 15V, R_G = 23Ω	
E_{on}	Turn-On Switching Loss	—	0.95	—	mJ	Energy losses include "tail"	
E_{off}	Turn-Off Switching Loss	—	1.15	—		and diode reverse recovery	
E_{ts}	Total Switching Loss	—	2.10	2.6		See Fig. 9,10,18	
t_{sc}	Short Circuit Withstand Time	10	—	—	µs	V_{CC} = 720V, T_J = 125°C V_{GE} = 15V, R_G = 5.0Ω	
$t_{d(on)}$	Turn-On Delay Time	—	42	—	ns	T_J = 150°C, See Fig. 10,11,18	
t_r	Rise Time	—	79	—		I_C = 10A, V_{CC} = 800V	
$t_{d(off)}$	Turn-Off Delay Time	—	540	—		V_{GE} = 15V, R_G = 23Ω,	
t_f	Fall Time	—	97	—		Energy losses include "tail"	
E_{ts}	Total Switching Loss	—	3.5	—	mJ	and diode reverse recovery	
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package	
C_{ies}	Input Capacitance	—	800	—	pF	V_{GE} = 0V	
C_{oes}	Output Capacitance	—	60	—		V_{CC} = 30V See Fig. 7	
C_{res}	Reverse Transfer Capacitance	—	14	—		ƒ = 1.0MHz	
t_{rr}	Diode Reverse Recovery Time	—	50	76	ns	T_J = 25°C See Fig.	
		—	72	110		T_J = 125°C 14	I_F = 10A
I_{rr}	Diode Peak Reverse Recovery Current	—	4.4	7.0	A	T_J = 25°C See Fig.	
		—	5.9	8.8		T_J = 125°C 15	V_R = 200V
Q_{rr}	Diode Reverse Recovery Charge	—	130	200	nC	T_J = 25°C See Fig.	
		—	250	380		T_J = 125°C 16	di/dt = 200A/µs
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery	—	210	—	A/µs	T_J = 25°C See Fig.	
	During t_b	—	180	—		T_J = 125°C 17	

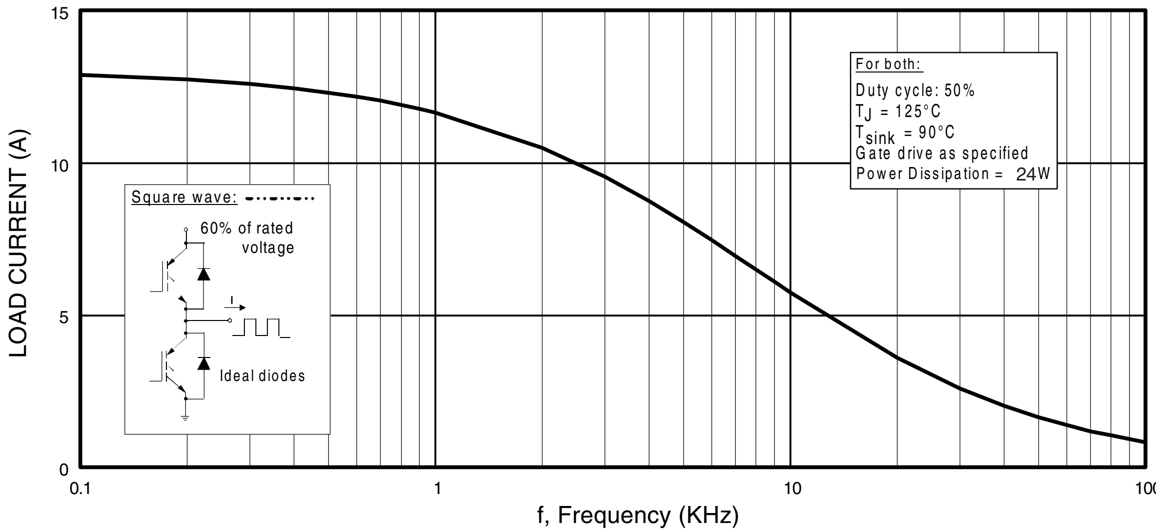


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

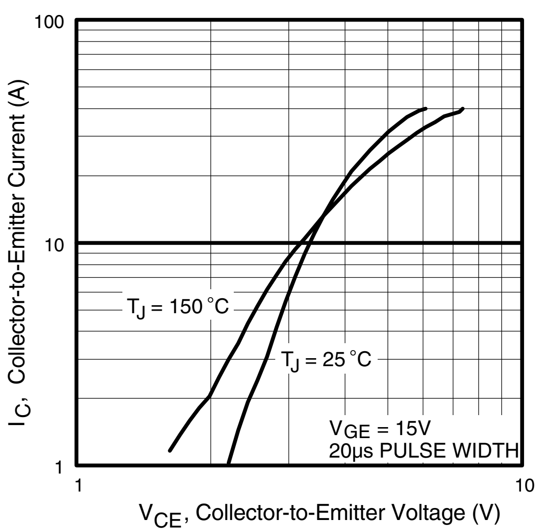


Fig. 2 - Typical Output Characteristics

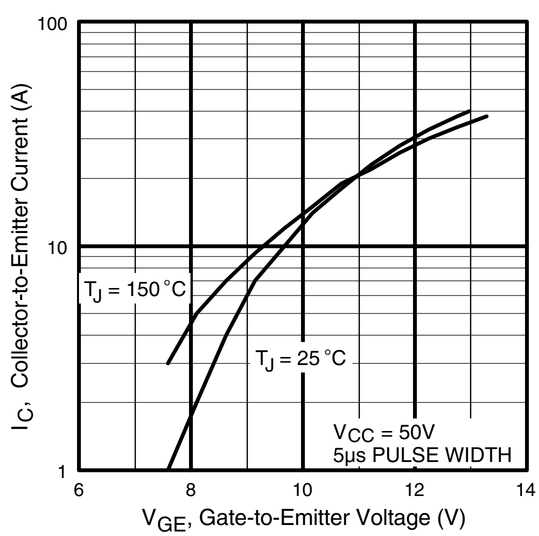


Fig. 3 - Typical Transfer Characteristics

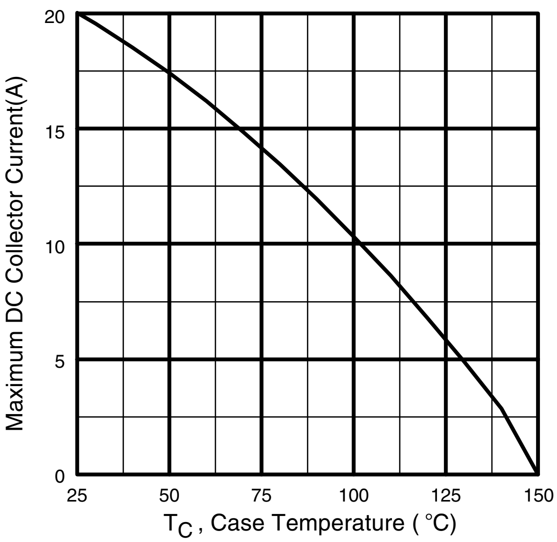


Fig. 4 - Maximum Collector Current vs. Case Temperature

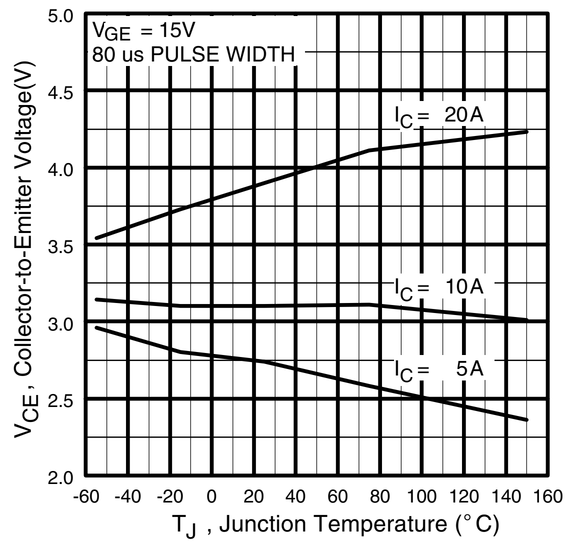


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

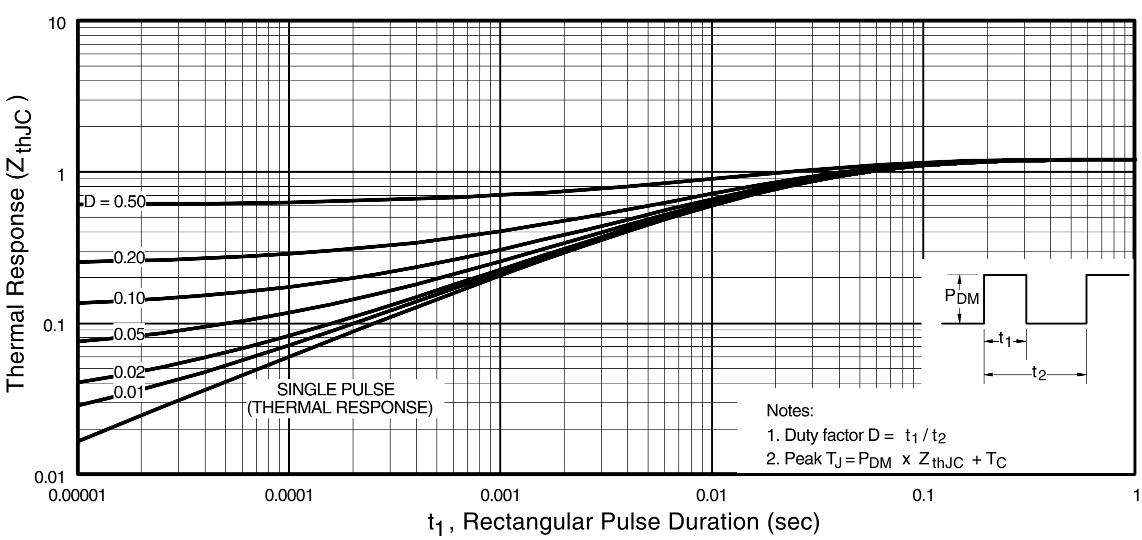


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

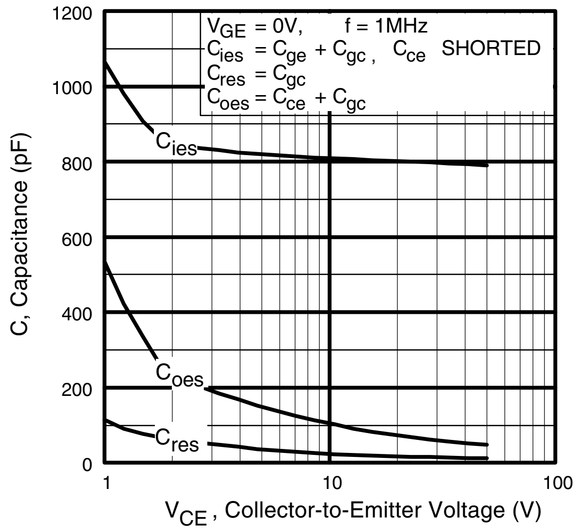


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

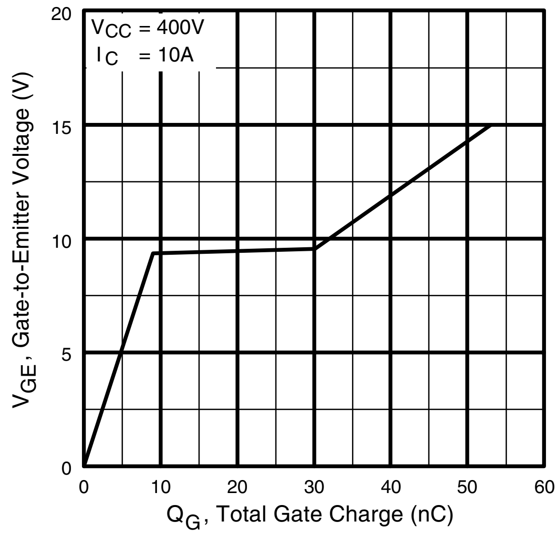


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

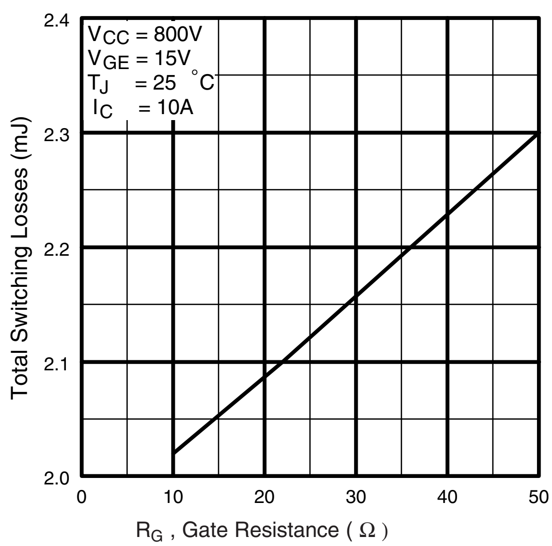


Fig. 9 - Typical Switching Losses vs. Gate Resistance

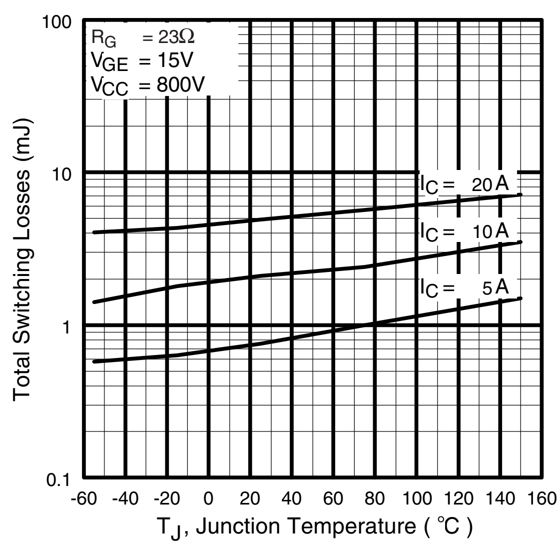


Fig. 10 - Typical Switching Losses vs. Junction Temperature

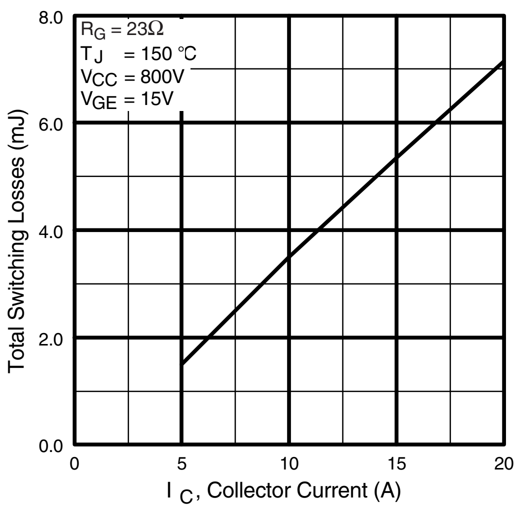


Fig. 11 - Typical Switching Losses vs. Collector Current

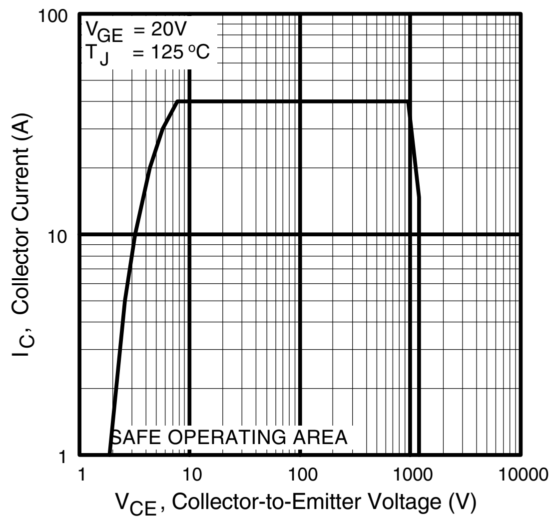


Fig. 12 - Turn-Off SOA

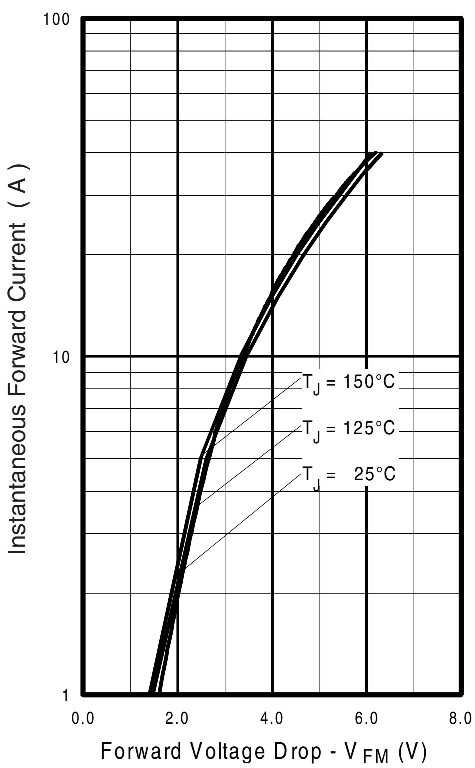


Fig. 13 - Typical Forward Voltage Drop vs. Instantaneous Forward Current

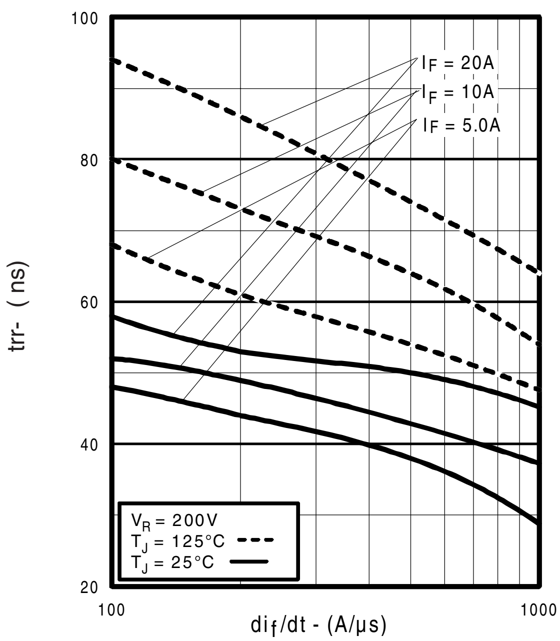


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

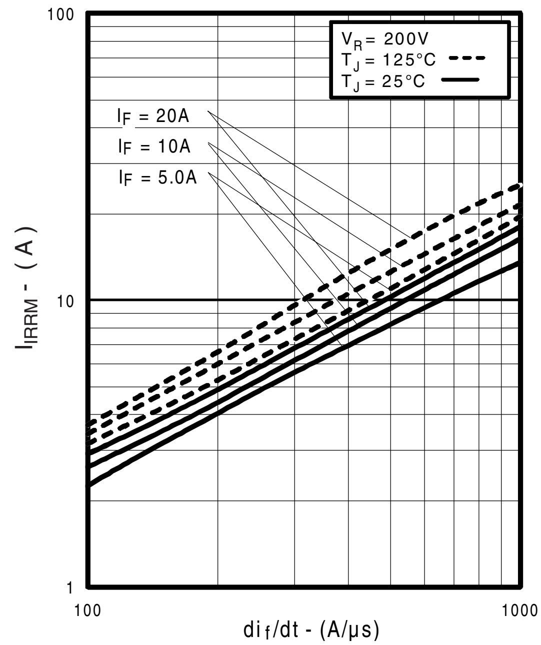


Fig. 15 - Typical Recovery Current vs. di_f/dt

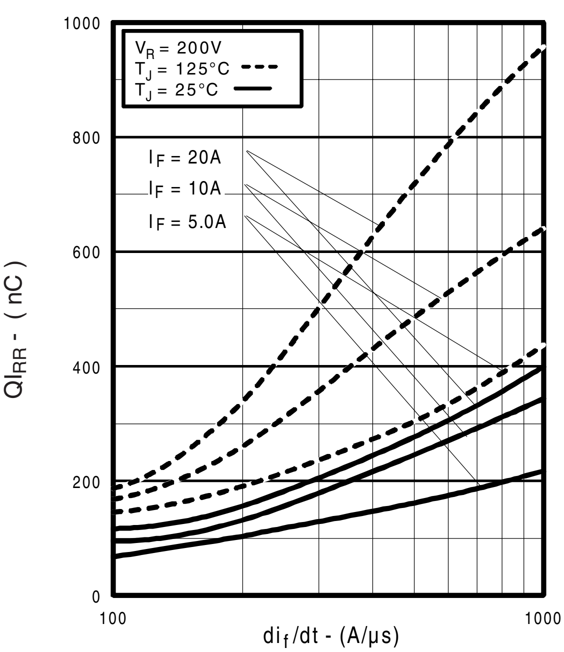


Fig. 16 - Typical Stored Charge vs. di_f/dt

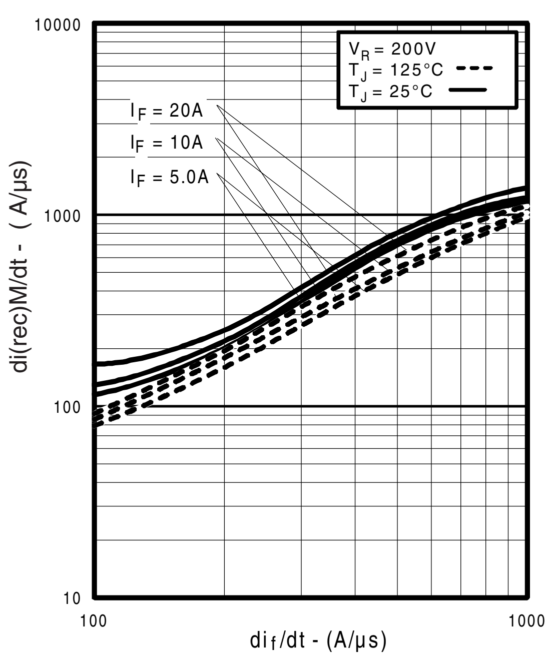


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

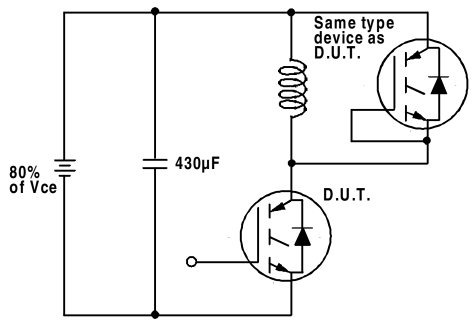


Fig. 18a - Test Circuit for Measurement of I_{LM}, E_{on}, $E_{off(diode)}$, t_{rr}, Q_{rr}, I_{rr}, $t_{d(on)}$, t_r, $t_{d(off)}$, t_f

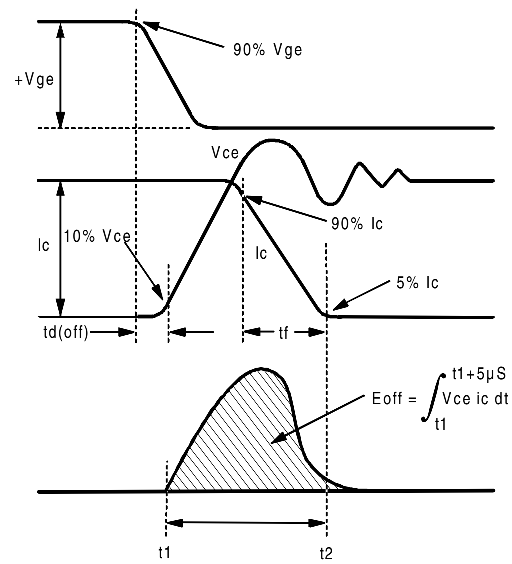


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off}, $t_{d(off)}$, t_f

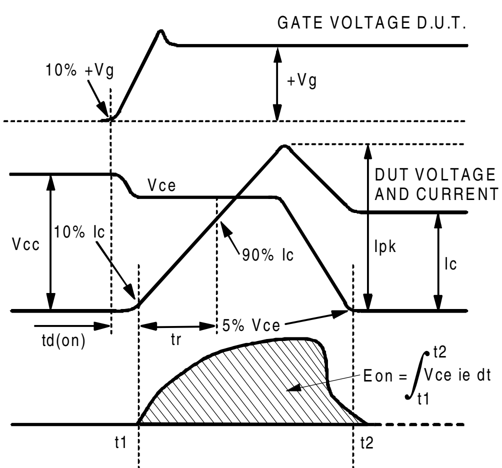


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on}, $t_{d(on)}$, t_r

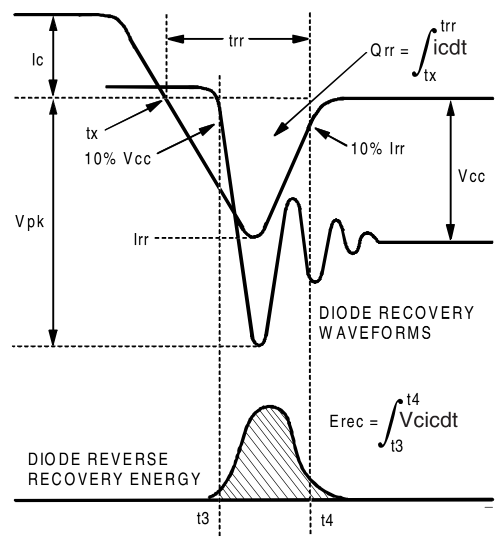


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec}, t_{rr}, Q_{rr}, I_{rr}

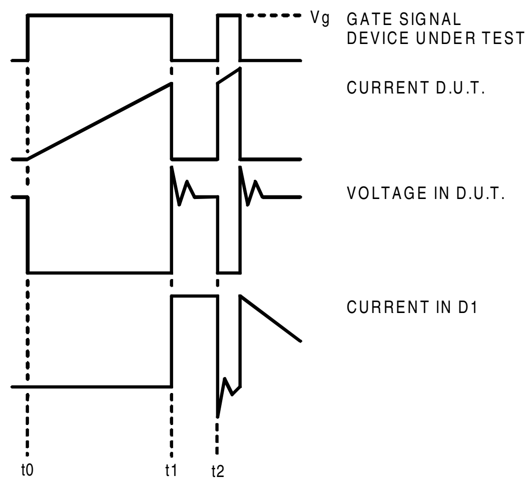


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

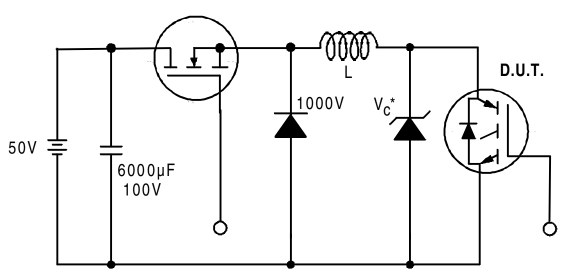


Figure 19. Clamped Inductive Load Test Circuit

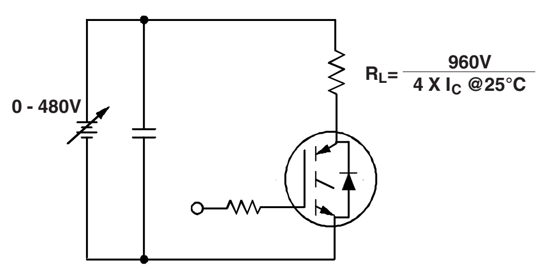


Figure 20. Pulsed Collector Current Test Circuit

Notes:

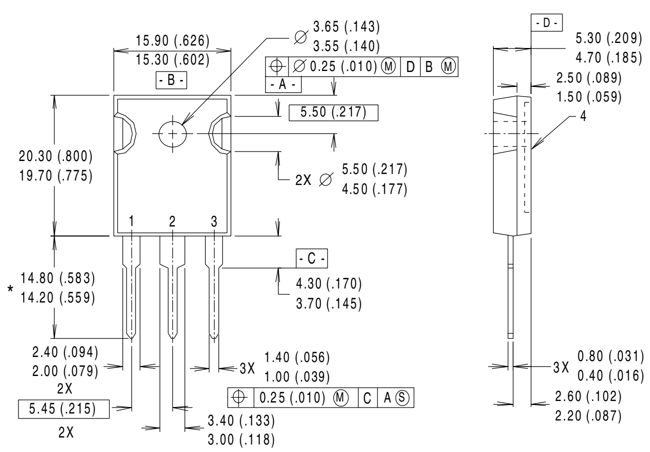
① Repetitive rating: V_{GE}=20V; pulse width limited by maximum junction temperature (figure 20)

② V_{CC}=80%(V_{CES}), V_{GE}=20V, L=10µH, R_G= 23Ω (figure 19)

③ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

④ Pulse width 5.0µs, single shot.

Case Outline — TO-247AC



NOTES:
1. DIMENSIONS & TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN MILLIMETERS (INCHES).
4. CONFORMS TO JEDEC OUTLINE TO-247AC.

LEAD ASSIGNMENTS
1 - GATE
2 - COLLECTOR
3 - EMITTER
4 - COLLECTOR

* LONGER LEADED (20mm) VERSION AVAILABLE (TO-247AD) TO ORDER ADD "-E" SUFFIX TO PART NUMBER

CONFORMS TO JEDEC OUTLINE TO-247AC (TO-3P)
Dimensions in Millimeters and (Inches)

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
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Data and specifications subject to change without notice. 6/00

Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/